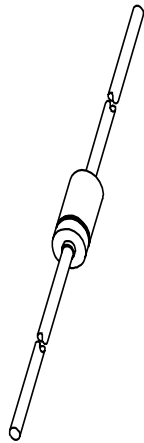


DATA SHEET



1N4531; 1N4532 High-speed diodes

Product data sheet
Supersedes data of April 1996

1996 Sep 03

High-speed diodes

1N4531; 1N4532

FEATURES

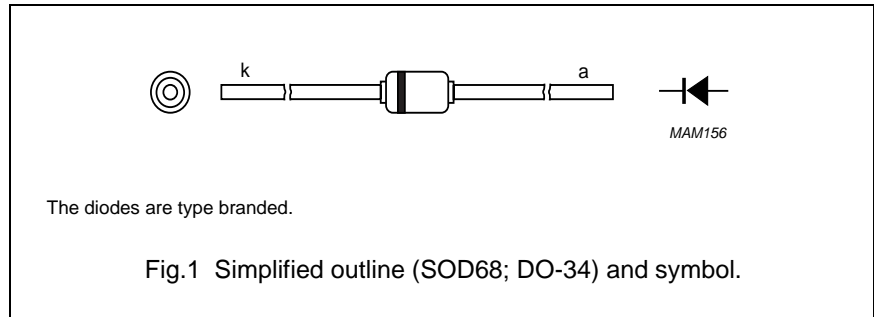
- Hermetically sealed leaded glass SOD68 (DO-34) package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching
- Protection diodes in reed relays.

DESCRIPTION

The 1N4531, 1N4532 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD68 (DO-34) packages.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		–	75	V
V _{RRM}	repetitive peak reverse voltage		–	75	V
I _F	continuous forward current	see Fig.2	–	200	mA
I _{FRM}	repetitive peak forward current		–	450	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4 t = 1 μs t = 1 ms t = 1 s	–	4 1 0.5	A A A
P _{tot}	total power dissipation	T _{amb} = 25 °C	–	500	mW
T _{stg}	storage temperature		–65	+200	°C
T _j	junction temperature		–	200	°C

High-speed diodes

1N4531; 1N4532

ELECTRICAL CHARACTERISTICST_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _F	forward voltage	I _F = 10 mA; see Fig.3	–	1000	mV
I _R	reverse current	see Fig.5			
	IN4531	V _R = 20 V	–	25	nA
		V _R = 20 V; T _j = 150 °C	–	50	μA
	IN4532	V _R = 50 V	–	100	nA
		V _R = 50 V; T _j = 150 °C	–	100	μA
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6			
	IN4531		–	4	pF
	IN4532		–	2	pF
t _{rr}	reverse recovery time	when switched from I _F = 10 mA to I _R = 60 mA; R _L = 100 Ω; measured at I _R = 1 mA; see Fig.7			
	IN4531		–	4	ns
	IN4532		–	2	ns
	reverse recovery time	when switched from I _F = 10 mA to I _R = 10 mA; R _L = 100 Ω; measured at I _R = 1 mA; see Fig.7			
	IN4532		–	4	ns
V _{fr}	forward recovery voltage	when switched from I _F = 100 mA; t _r ≤ 30 ns; see Fig.8	–	3	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length 5 mm	120	K/W
R _{th j-a}	thermal resistance from junction to ambient	lead length 5 mm; note 1	350	K/W

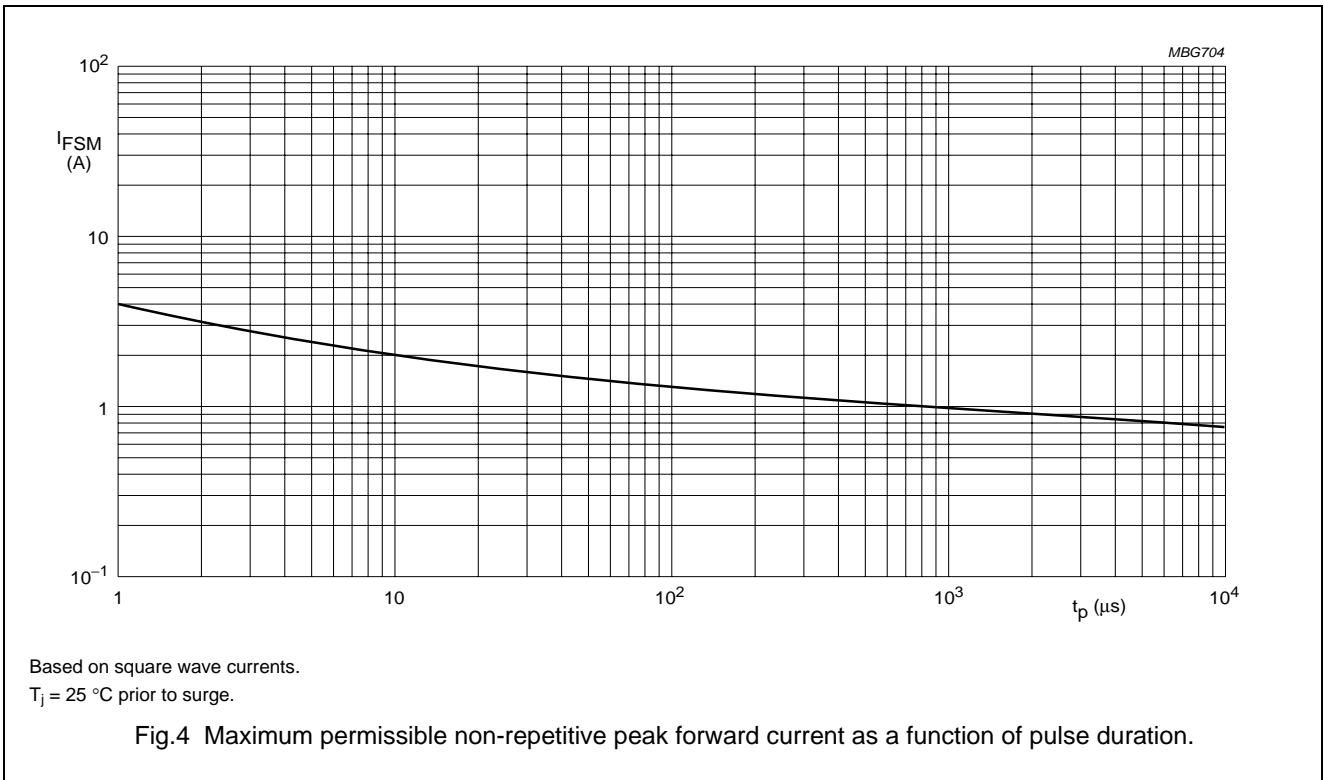
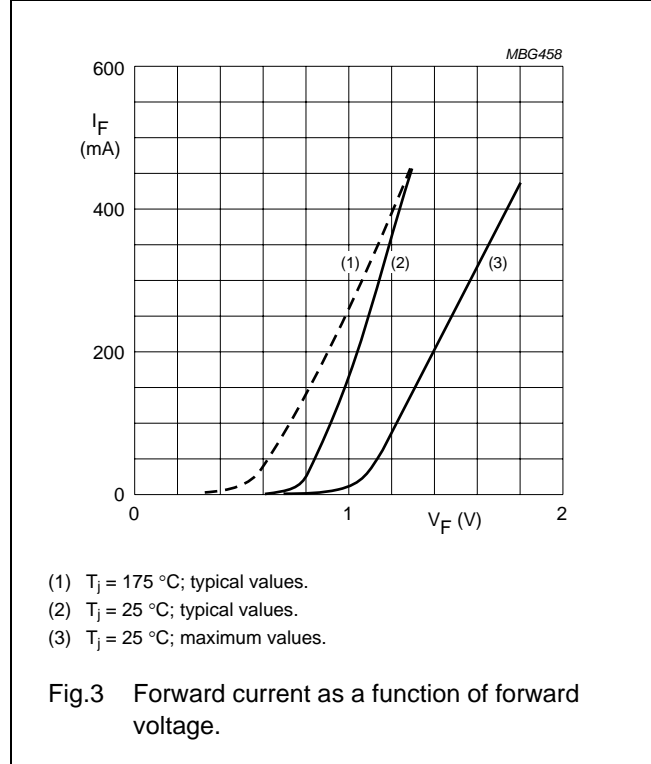
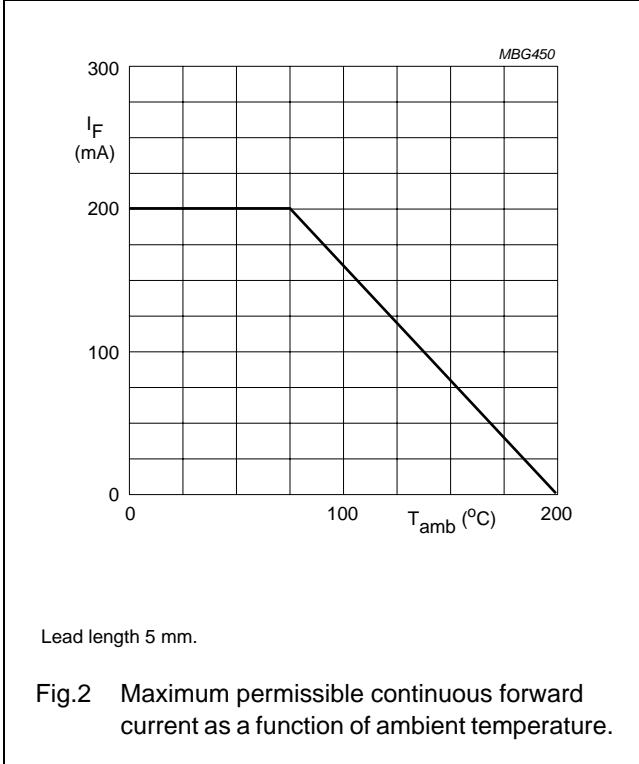
Note

1. Device mounted on a printed circuit-board without metallization pad.

High-speed diodes

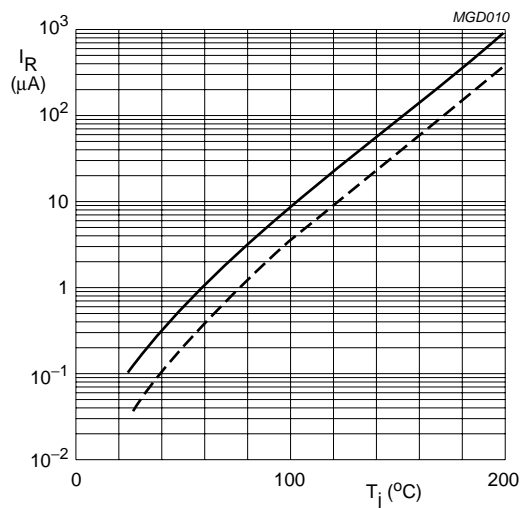
1N4531; 1N4532

GRAPHICAL DATA



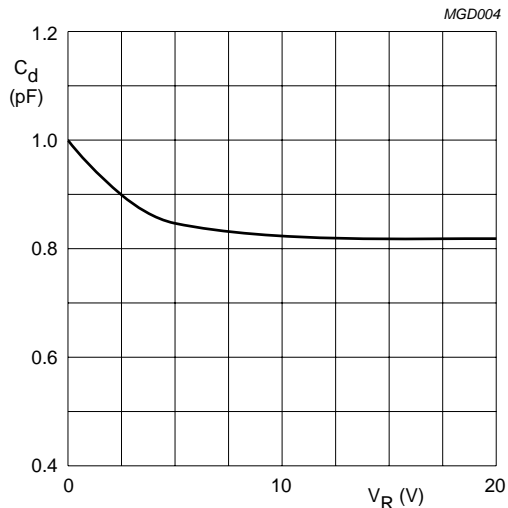
High-speed diodes

1N4531; 1N4532



$V_R = 50$ V
 Solid line; maximum values.
 Dotted line; typical values.

Fig.5 Reverse current as a function of junction temperature.

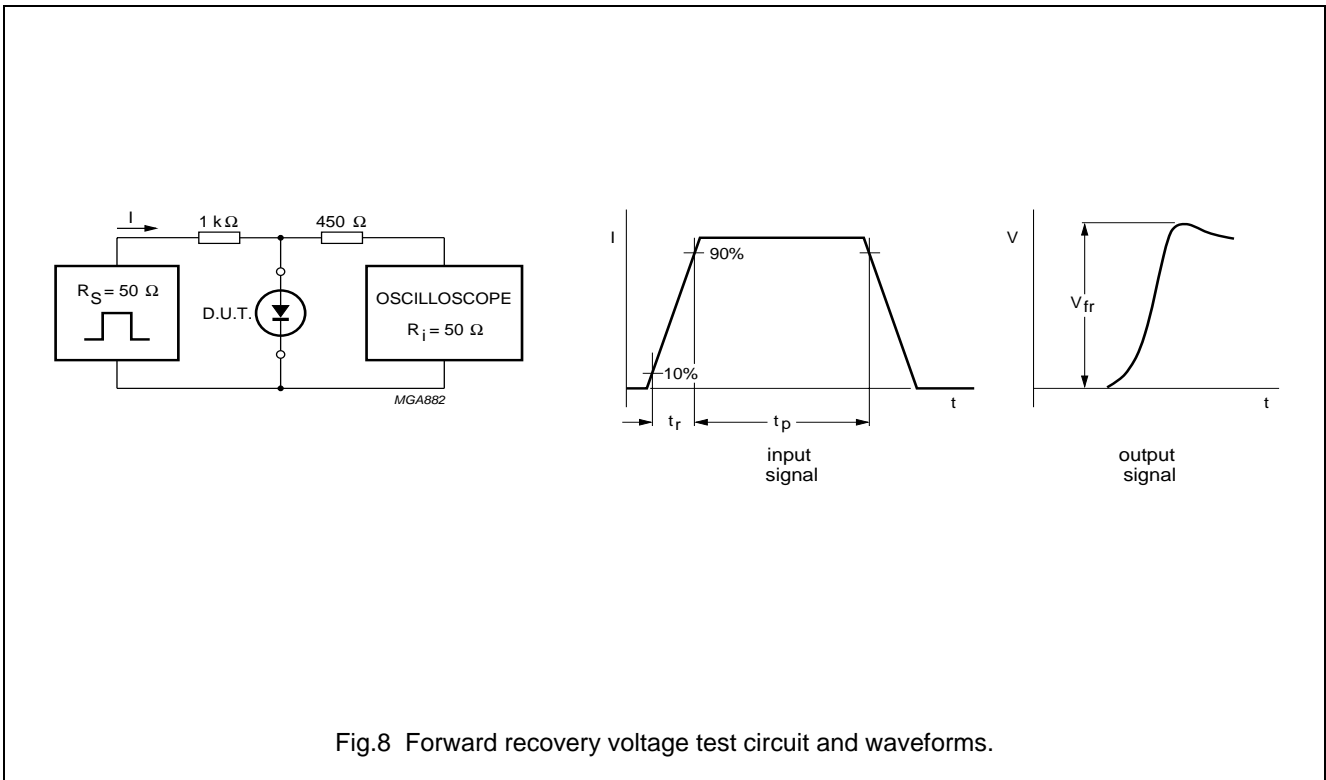
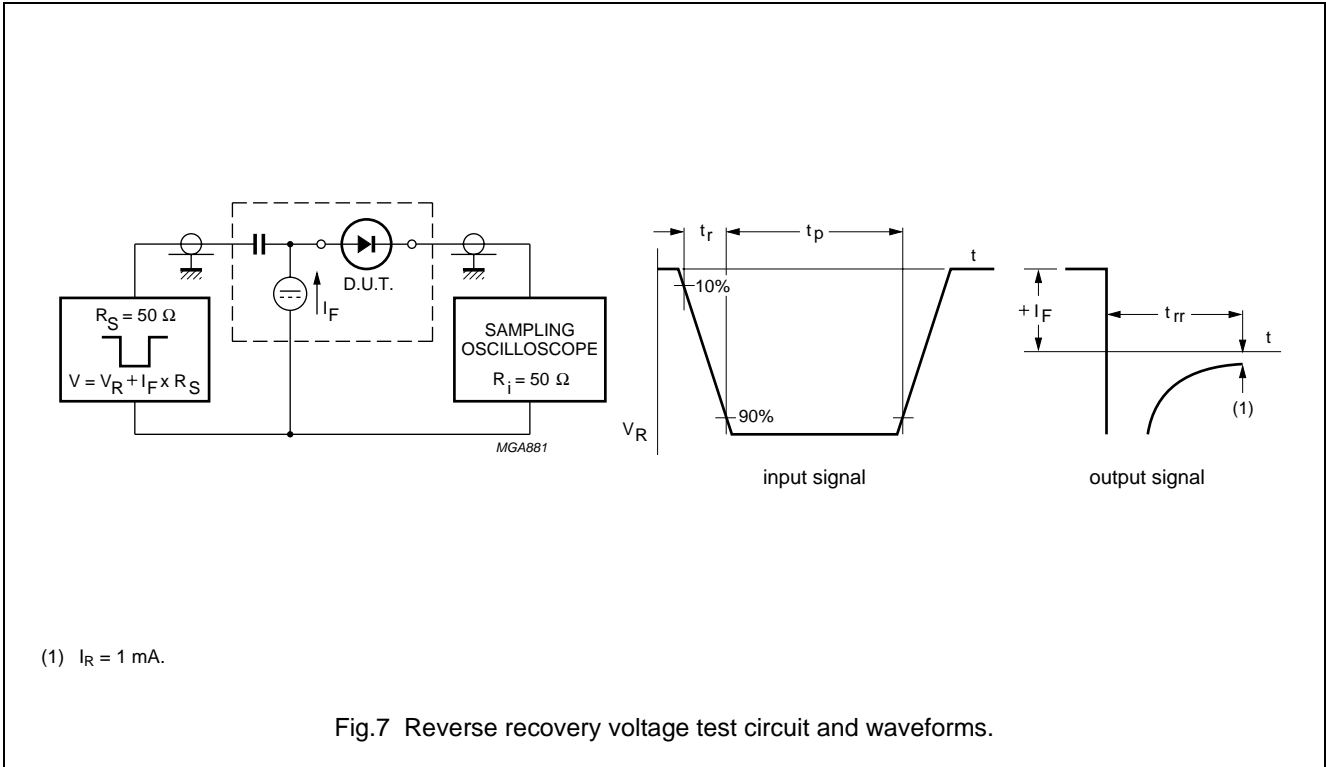


$f = 1$ MHz; $T_j = 25$ °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed diodes

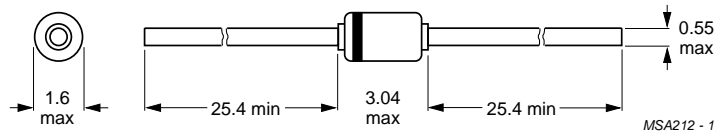
1N4531; 1N4532



High-speed diodes

1N4531; 1N4532

PACKAGE OUTLINE



Dimensions in mm.

Fig.9 SOD68 (DO-34).

High-speed diodes

1N4531; 1N4532

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

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